MGFC42V3742

3.7 ~ 4.2GHz BAND 16W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC42V3742 is an internally impedance-matched GaAs power FET especially designed for use in 3.7 ~ 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 16W (TYP.) @ f= $3.7 \sim 4.2$ GHz High power gain GLP = 11 dB (TYP.) @ f= $3.7 \sim 4.2$ GHz High power added efficiency P.A.E. = 32 % (TYP.) @ f= $3.7 \sim 4.2$ GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @Po=31(dBm) S.C.L.

APPLICATION

item 01 : 3.7~4.2 GHz band power amplifier item 51 : 3.7~4.2 GHz band digital radio communication

QUALITY GRADE

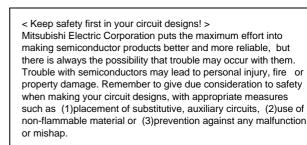
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RECOMMENDED BIAS CONDITIONS

VDS = 10(V)ID = 4.5 (A)Rg = 25(ohm) Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-15	V
ID	Drain current	15	А
IGR	Reverse gate current	-40	mA
IGF	Forward gate current	84	mA
PT	Total power dissipation *1	78.9	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C



*1 : Tc=25 deg.C

ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)

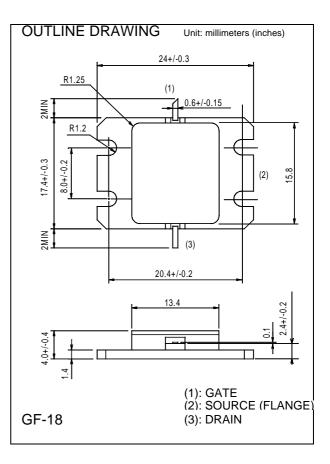
Symbol	Parameter	Test conditions	Limits			Unit
Symbol			Min.	Тур.	Max.	Unit
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	9	12	А
gm	Transconductance	VDS=3V, ID=4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=80mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression		41.5	42.5	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=4.5A, f=3.7~4.2GHz	9	11	-	dB
ID	Drain current		-	4.5	-	А
P.A.E.	Power added efficiency		-	32	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	-	1.9	deg.C/W

(Ta=25 deg.C)

*1 : item -51, 2 tone test, Po=31dBm Single Carrier Level, f=4.2GHz, Delta f=10MHz

*2 : Channel to case





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